

Abstract

A laser system 1 is composed of a temperature control section 12 that has a Peltier device 9, a heat sink 10, and a base plate 11; and a laser section 8 that has a laser diode 2, a lens 3, a grating 5, a first support member 5, and second support member 6. The heat sink 10 is connected to the base plate 11 and is perpendicular thereto. The Peltier device 9 is connected to the heat sink 10. The second support member 6 of the laser section 8 is connected to the Peltier device 9 so that one surface of the Peltier device 9 is connected to the heat sink 10 and the other surface of the Peltier device 9 is connected to the second support member 6. Heat generated in the laser diode 2, the lens 3, the first support member 5, and so forth, which compose an external cavity type semiconductor laser, is transmitted through the second support member 6, the Peltier device 9, the heat sink 10, and the base plate 11. When the distance by which the base plate 11 and the laser section 8 are spaced apart is a predetermined value or more, heat transmitted to the laser section 8 can be effectively blocked.